onsemi

2 A Output Current, High Speed MOSFET Gate Driver Optocoupler

FOD3180

Description

The FOD3180 is a 2 A Output Current, High Speed MOSFET Gate Drive Optocoupler. It consists of a aluminium gallium arsenide (AlGaAs) light emitting diode optically coupled to a CMOS detector with PMOS and NMOS output power transistors integrated circuit power stage. It is ideally suited for high frequency driving of power MOSFETs used in Plasma Display Panels (PDPs), motor control inverter applications and high performance DC/DC converters.

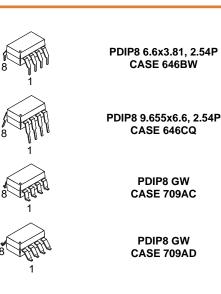
The device is packaged in an 8–pin dual in–line housing compatible with 260°C reflow processes for lead free solder compliance.

Features

- Guaranteed Operating Temperature Range of -40°C to +100°C
- 2 A Minimum Peak Output Current
- High Speed Response: 200 ns Max Propagation Delay over Temperature Range
- 250 kHz Maximum Switching Speed
- 30 ns Typ Pulse Width Distortion
- Wide V_{CC} Operating Range: 10 V to 20 V
- 5000 Vrms, 1 Minute Isolation
- Under Voltage Lockout Protection (UVLO) with Hysteresis
- Minimum Creepage Distance of 7.0 mm
- Minimum Clearance Distance of 7.0 mm
- C–UL, UL and VDE* Approved
- $R_{DS(ON)}$ of 1.5 Ω (Typ.) Offers Lower Power Dissipation
- 15 kV/µs Minimum Common Mode Rejection
- These are Pb–Free Devices

Applications

- Plasma Display Panel
- High Performance DC/DC Convertor
- High Performance Switch Mode Power Supply
- High Performance Uninterruptible Power Supply
- Isolated Power MOSFET Gate Drive
- *Requires "V" ordering option

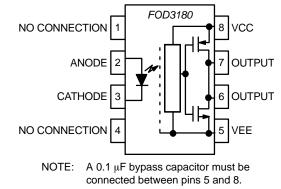


MARKING DIAGRAM



- 3180 = Device Number
- VDE Mark (NOTE: Only Appears on Parts Ordered with VDE Option – See Order Table)
- XX = Two Digit Year Code, e.g., '03'
- YY = Two Digit Work Week, Ranging from '01' to '53'
- B = Assembly Package Code

FUNCTIONAL BLOCK DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-40 to +125	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
TJ	Junction Temperature	-40 to +125	°C
TSOL	Lead Solder Temperature	260 for 10 sec.	°C
I _{F(AVG)}	Average Input Current (Note 1)	25	mA
I _{F(tr, tf)}	LED Current Minimum Rate of Rise/Fall	250	ns
I _{F(TRAN)}	Peak Transient Input Current (<1 μs Pulse Width, 300 pps)	1.0	А
V _R	Reverse Input Voltage	5	V
I _{OH(PEAK)}	"High" Peak Output Current (Note 2)	2.5	А
I _{OL(PEAK)}	"Low" Peak Output Current (Note 2)	2.5	А
$V_{CC} - V_{EE}$	Supply Voltage	-0.5 to 25	V
V _{O(PEAK)}	Output Voltage	0 to V _{CC}	V
P _O	Output Power Dissipation (Note 3)	250	mW
PD	Total Power Dissipation (Note 4)	295	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Derate linearly above +70°C free air temperature at a rate of 0.3 mA/°C.

2. The output currents I_{OH} and I_{OL} are specified with a capacitive current limited load = (3 x 0.01 μ F) + 0.5 Ω , frequency = 8 kHz, 50% DF. 3. Derate linearly above +87°C, free air temperature at the rate of 0.77 mW/°C. Refer to Figure 13.

4. No derating required across operating temperature range.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
$V_{CC} - V_{EE}$	Power Supply	10 to 20	V
I _{F(ON)}	Input Current (ON)	10 to 16	mA
V _{F(OFF)}	Input Voltage (OFF)	-3.0 to 0.8	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Symbol	Parameter	Test Conditions	Min	Тур*	Max	Unit
I _{OH}	High Level Output Current (Note 5) (Note 6)	$V_{OH} = (V_{CC} - V_{EE} - 1 V)$	0.5	-	-	А
		$V_{OH} = (V_{CC} - V_{EE} - 3 V)$	2.0	-	-	
I _{OL}	Low Level Output Current (Note 5) (Note 6)	$V_{OL} = (V_{CC} - V_{EE} - 1 V)$	0.5	-	-	А
		$V_{OL} = (V_{CC} - V_{EE} - 3 V)$	2.0	-	-	
V _{OH}	High Level Output Voltage (Note 7) (Note 8)	I _O = -100 mA	$V_{CC} - 0.5$	-	-	V
V _{OL}	Low Level Output Voltage (Note 7) (Note 8)	I _O = 100 mA	-	-	V _{EE} + 0.5	V
I _{CCH}	High Level Supply Current	Output Open, I _F = 10 to 16 mA	-	4.8	6.0	mA
I _{CCL}	Low Level Supply Current	Output Open, $V_F = -3.0$ to 0.8 V	-	5.0	6.0	mA
I _{FLH}	Threshold Input Current Low to High	$I_{O} = 0 \text{ mA}, V_{O} > 5 \text{ V}$	-	-	8.0	mA
V _{FHL}	Threshold Input Voltage High to Low	$I_{O} = 0 \text{ mA}, V_{O} < 5 \text{ V}$	0.8	-	-	V
V _F	Input Forward Voltage	I _F = 10 mA	1.2	1.43	1.8	V
$\Delta V_{F} / T_{A}$	Temperature Coefficient of Forward Voltage	I _F = 10 mA	-	-1.5	-	mV/°C
VU _{VLO+}	UVLO Threshold	$V_{O} > 5 V$, $I_{F} = 10 mA$	-	8.3	-	V
V _{UVLO-}		V _O < 5 V, I _F = 10 mA	-	7.7	-	V
UVLO _{HYST}	UVLO Hysteresis		-	0.6	-	V
BV _R	Input Reverse Breakdown Voltage	I _R = 10 μA	5	-	-	V
CIN	Input Capacitance	f = 1 MHz, V _F = 0 V	-	60	-	pF

ELECTRICAL-OPTICAL CHARACTERISTICS	(DC)	Over recommended operating conditions unless otherwise specif	ied.)

*Typical values at $T_A = 25^{\circ}C$

5. The output currents I_{OH} and I_{OL} are specified with a capacitive current limited load = (3 x 0.01 μ F) + 0.5 Ω , frequency = 8 kHz, 50% DF.

6.

The output currents I_{OH} and I_{OL} are specified with a capacitive current limited load = (3 x 0.01 μ F) + 8.5 Ω , frequency = 8 kHz, 50% DF. In this test, V_{OH} is measured with a dc load current of 100 mA. When driving capacitive load V_{OH} will approach V_{CC} as I_{OH} approaches zero 7. amps.

8. Maximum pulse width = 1 ms, maximum duty cycle = 20%.

SWITCHING CHARACTERISTICS (Over recommended operating conditions unless otherwise specified.)

Symbol	Parameter	Test Conditions	Min	Тур*	Max	Unit
t _{PLH}	Propagation Delay Time to High Output Level (Note 9)	$I_F = 10$ mA, $R_g = 10 \Omega$, f = 250 kHz, Duty Cycle = 50%,	50	135	200	ns
t _{PHL}	Propagation Delay Time to Low Output Level (Note 9)	C _g = 10 nF	50	105	200	ns
P _{WD}	Pulse Width Distortion (Note 10)		_	-	65	ns
P _{DD} (t _{PHL} – t _{PLH})	Propagation Delay Difference Between Any Two Parts (Note 11)		-90	-	90	ns
t _r	Rise Time	C_L = 10nF, R_g = 10 Ω	-	75	-	ns
t _f	Fall Time		-	55	-	ns
t _{UVLO ON}	UVLO Turn On Delay		-	2.0	-	μs
t _{UVLO OFF}	UVLO Turn Off Delay		-	0.3	-	μs
CM _H	Output High Level Common Mode Transient Immunity (Note 12) (Note 13)	$T_A = +25^{\circ}C$, $I_f = 10$ to 16 mA, $V_{CM} = 1.5$ kV, $V_{CC} = 20$ V	15	-	-	kV/μs
CM _L	Output Low Level Common Mode Transient Immunity (Note 12) (Note 14)	$T_A = +25^{\circ}C, V_f = 0 V,$ $V_{CM} = 1.5 \text{ kV}, V_{CC} = 20 \text{ V}$	15	-	-	kV/μs

*Typical values at $T_A = 25^{\circ}C$

9. t_{PHL} propagation delay is measured from the 50% level on the falling edge of the input pulse to the 50% level of the falling edge of the V_O signal. tPLH propagation delay is measured from the 50% level on the rising edge of the input pulse to the 50% level of the rising edge of the V_O signal.

10. $\ensuremath{\text{PWD}}$ is defined as $|\ensuremath{\,t_{\text{PHL}}}-\ensuremath{\,t_{\text{PLH}}}|$ for any given device.

11. The difference between tPHL and tPLH between any two FOD3180 parts under same test conditions.

12. Pin 1 and 4 need to be connected to LED common.

13. Common mode transient immunity in the high state is the maximum tolerable dV_{CM}/dt of the common mode pulse V_{CM} to assure that the output will remain in the high state (i.e. $V_0 > 10.0$ V).

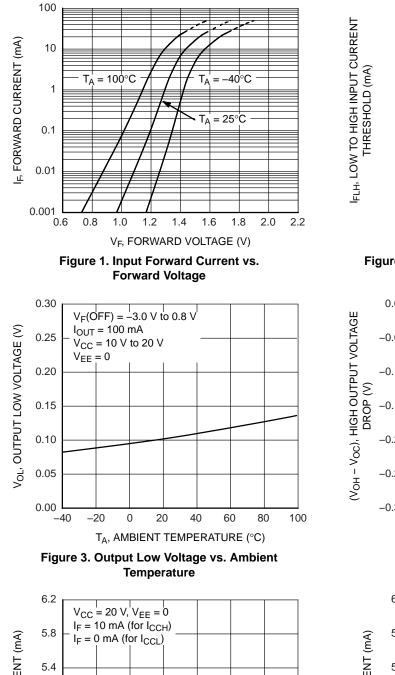
14. Common mode transient immunity in a low state is the maximum tolerable dV_{CM}/dt of the common mode pulse, V_{CM}, to assure that the output will remain in a low state (i.e. $V_O < 1.0$ V).

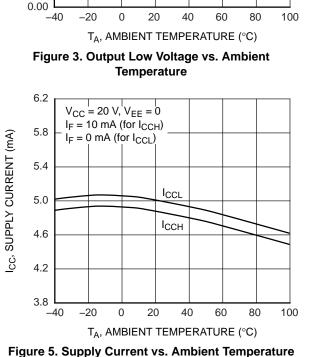
ISOLATION CHARACTERISTICS

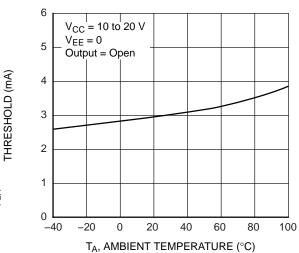
Symbol	Parameter	Test Conditions	Min	Тур*	Max	Unit
V _{ISO}	Withstand Isolation Voltage (Note 15) (Note 16)	$T_A = 25^{\circ}C, R.H. < 50\%, t = 1 min., I_{I-O} \le 20 \mu A$	5000	-	-	Vrms
R _{I-O}	Resistance (Input to Output) (Note 16)	V _{I-O} = 500 V	-	10 ¹¹	-	Ω
C _{I-O}	Capacitance (Input to Output)	Freq. = 1 MHz	-	1	-	pF

*Typical values at T_A = 25°C
15. In accordance with UL 1577, each optocoupler is proof tested by applying an insulation test voltage > 6000 Vrms, 60 Hz for 1 second (leakage detection current limit I_{I-O} < 5 μA).
16. Device considered a two-terminal device: pins on input side shorted together and pins on output side shorted together.

TYPICAL PERFORMANCE CURVES









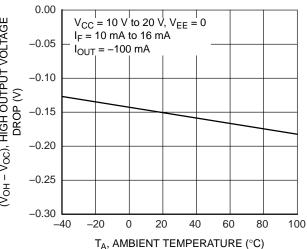


Figure 4. High Output Voltage Drop vs. Ambient Temperature

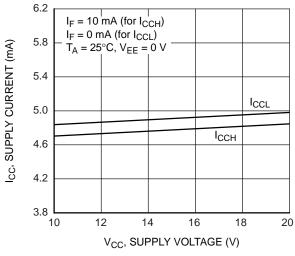
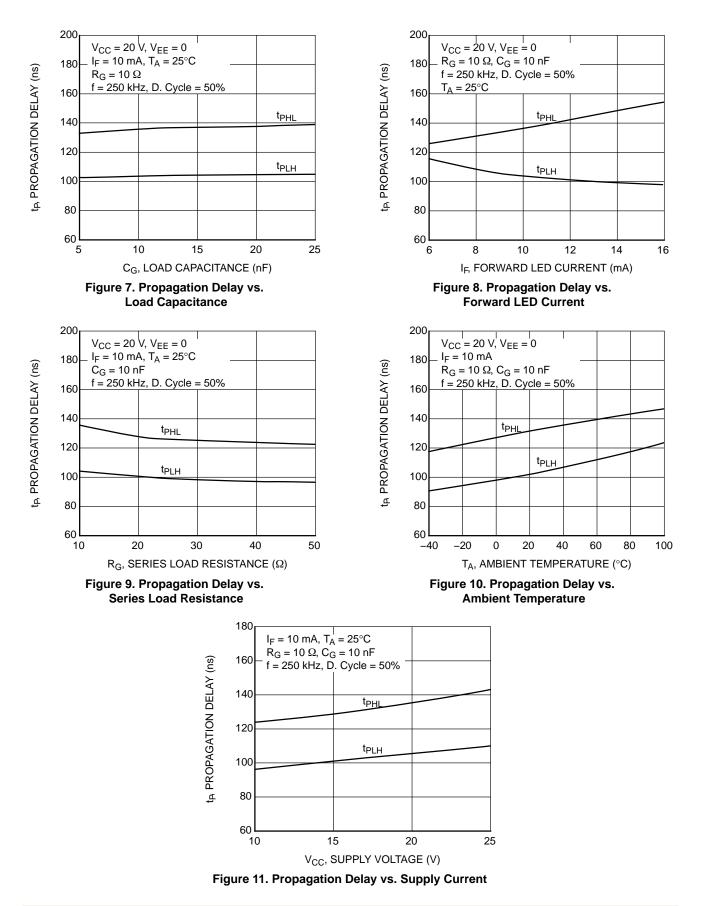
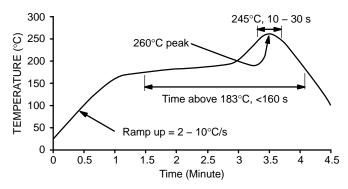


Figure 6. Supply Current vs. Supply Voltage

TYPICAL PERFORMANCE CURVES (continued)



REFLOW PROFILE



Peak reflow temperature: 260°C (package surface temperature)

Time of temperature higher than 183°C for 160 seconds or less

• One time soldering reflow is recommended



OUTPUT POWER DERATING

The maximum package power dissipation is 295 mW. The package is limited to this level to ensure that under normal operating conditions and over extended temperature range that the semiconductor junction temperatures do not exceed 125°C. The package power is composed of three elements; the LED, static operating power of the output IC, and the power dissipated in the output power MOSFET transistors. The power rating of the output IC is 250 mW. This power is divided between the static power of the integrated circuit, which is the product of IDD times the power supply voltage $(V_{DD} - V_{EE})$. The maximum IC static output power is 150 mW, $(V_{DD} - V_{EE}) = 25$ V, $I_{DD} = 6$ mA. This maximum condition is valid over the operational temperature range of -40° C to $+100^{\circ}$ C. Under these maximum operating conditions, the output of the power MOSFET is allowed to dissipate 100 mW of power.

The absolute maximum output power dissipation versus ambient temperature is shown in Figure 13. The output driver is capable of supplying 100 mW of output power over the temperature range from -40° C to 87° C. The output derates to 90 mW at the absolute maximum operating temperature of 100°C.

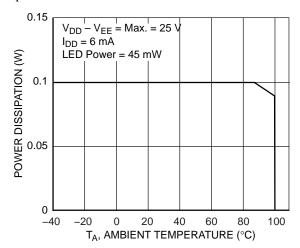


Figure 13. Absolute Maximum Power Dissipation vs. Ambient Temperature

The output power is the product of the average output current squared times the output transistor's $R_{DS(ON)}$:

$$P_{O(AVG)} = I_{O(AVG)} 2 \cdot R_{DS(ON)}$$
(eq. 1)

The $I_{O(AVG)}$ is the product of the duty factor times the peak current flowing in the output. The duty factor is the ratio of the 'on' time of the output load current divided by the period of the operating frequency. An $R_{DS(ON)}$ of 2.0 Ω results in an average output load current of 200 mA. The load duty factor is a ratio of the average output time of the power MOSFET load circuit and period of the driving frequency.

The maximum permissible, operating frequency is determined by the load supplied to the output at its resulting output pulse width. Figure 14 shows an example of a 0.03 μ F gate to source capacitance with a series resistance of 8.50 Ω . This reactive load results in a composite average pulse width of 1.5 μ s. Under this load condition it is not necessary to derate the absolute maximum output current until the frequency of operation exceeds 63 kHz.

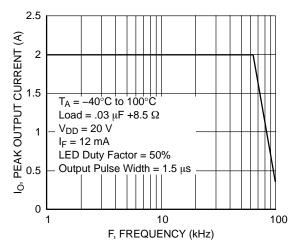


Figure 14. Output Current Derating vs. Frequency

IOH AND IOL TEST CONDITIONS

This device is tested and specified when driving a complex reactive load. The load consists of a capacitor in the series with a current limiting resistor. The capacitor represents the gate to source capacitance of a power MOSFET transistor. The test load is a 0.03 μ F capacitor in series with an 8.5 Ω resistor. The LED test frequency is 10.0 kHz with a 50% duty cycle. The combined I_{OH} and I_{OL} output load current duty factor is 0.6% at the test frequency.

Figure 15 illustrates the relationship of the LED input drive current and the device's output voltage and sourcing and sinking currents. The 0.03 μ F capacitor load rep

resents the gate to source capacitance of a very large power MOSFET transistor. A single supply voltage of 20 V is used in the evaluation.

Figure 16 shows the test schematic to evaluate the out– put voltage and sourcing and sinking capability of the device. The I_{OH} and I_{OL} are measured at the peak of their respective current pulses.

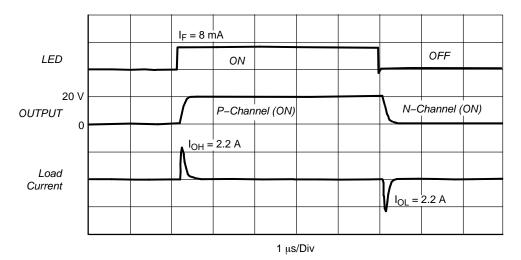


Figure 15. FOD 3180 Output Current and Output Voltage vs. LED Drive

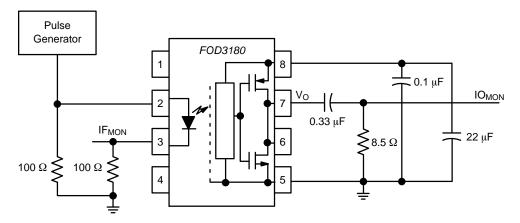


Figure 16. Test Schematic

ORDERING INFORMATION

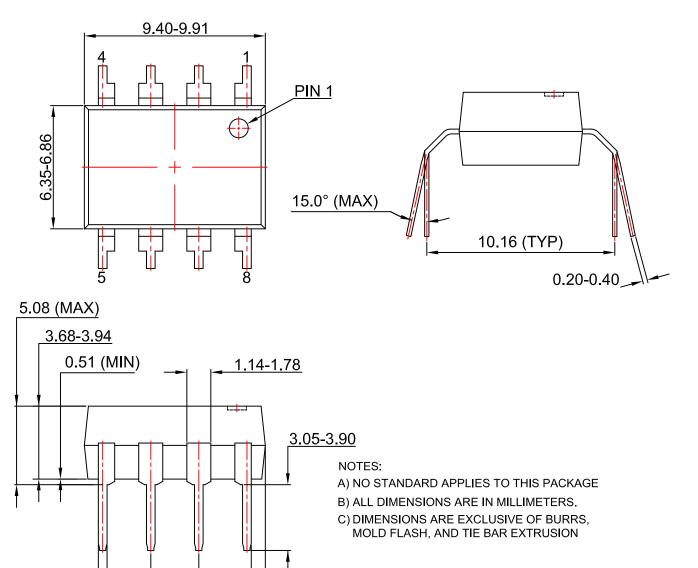
Option	Order Entry Identifier (Example)	Description [†]
No option	FOD3180	Standard Through Hole Device
S	FOD3180S	Surface Mount, Lead Bend
SD	FOD3180SD	Surface Mount, Tape and Reel
Т	FOD3180T	0.4" Lead Spacing
V	FOD3180V	VDE 0884
TV	FOD3180TV	VDE 0884, 0.4" Lead Spacing
SV	FOD3180SV	VDE 0884, Surface Mount
SDV	FOD3180SDV	VDE 0884, Surface Mount, Tape and Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



PDIP8 6.6x3.81, 2.54P CASE 646BW ISSUE O

DATE 31 JUL 2016



DOCUMENT NUMBER:	98AON13445G Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	PDIP8 6.6X3.81, 2.54P		PAGE 1 OF 1		

(0.78)

2.54 BSC

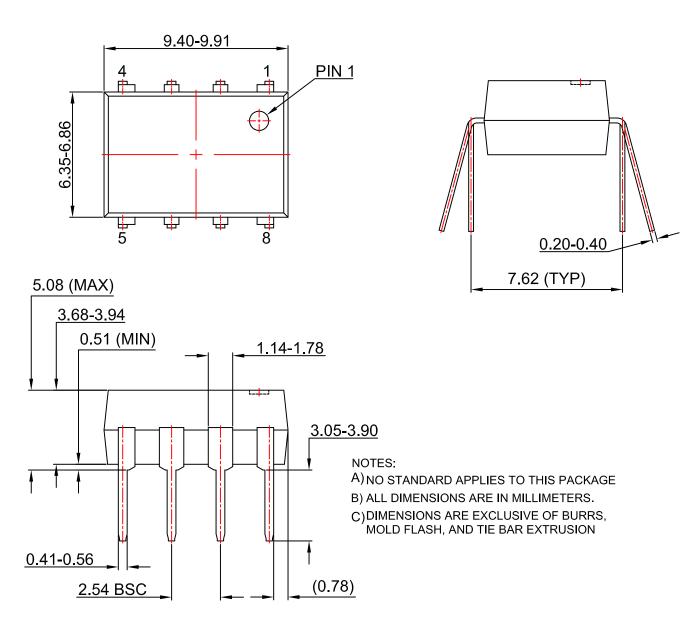
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights of others.

0.41-0.56



PDIP8 9.655x6.6, 2.54P CASE 646CQ ISSUE O

DATE 18 SEP 2017



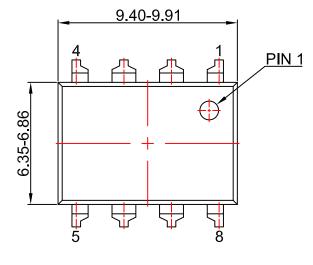
DOCUMENT NUMBER:	98AON13446G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	PDIP8 9.655X6.6, 2.54P		PAGE 1 OF 1		
the right to make changes without furth purpose, nor does onsemi assume as	er notice to any products herein. onsemi making in the second sec	LLC dba onsemi or its subsidiaries in the United States and/or other co es no warranty, representation or guarantee regarding the suitability of its of any product or circuit, and specifically disclaims any and all liability, ir e under its patent rights nor the rights of others.	products for any particular		

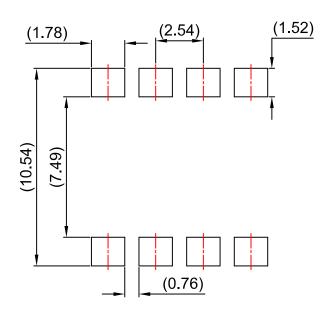
© Semiconductor Components Industries, LLC, 2017



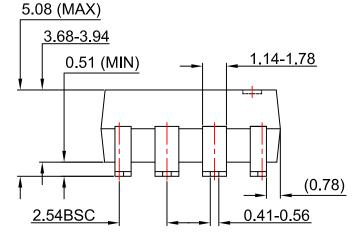
PDIP8 GW CASE 709AC ISSUE O

DATE 31 JUL 2016



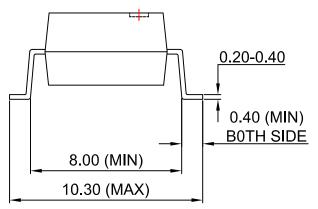


LAND PATTERN RECOMMENDATION



NOTES:

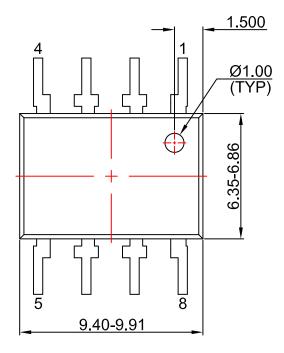
- A) NO STANDARD APPLIES TO THIS PACKAGE
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION

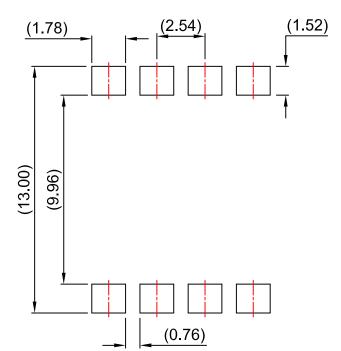


DOCUMENT NUMBER:	98AON13447G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	PDIP8 GW		PAGE 1 OF 1				
the right to make changes without furth purpose, nor does onsemi assume ar	onsemi and ONSEM) are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights or the rights of others.						

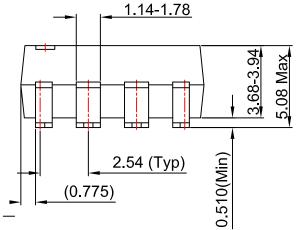
PDIP8 GW CASE 709AD ISSUE O

DATE 31 JUL 2016



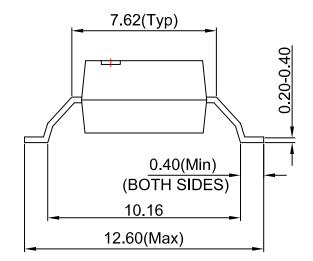


LAND PATTERN RECOMMENDATION



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION



DOCUMENT NUMBER:	98AON13448G Electronic versions are uncontrolled except when accessed directly from the Document Reposite Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	PDIP8 GW		PAGE 1 OF 1

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>